



Attorney Docket No.: SSI-00501

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	
Maximilian A. Biberger et al.	

Serial No.: 09/912,844

Filed: July 24, 2001

For: HIGH PRESSURE PROCESSING

CHAMBER FOR

SEMICONDUCTOR SUBSTRATE

Group Art Unit: 1763

Examiner: Ram N. Kackar

TRANSMITTAL LETTER

162 N. Wolfe Road Sunnyvale, CA 94086 (408) 530-9700

Customer No.: 28960

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313

Sir:

Enclosed please find a Supplemental Information Disclosure Statement and Form PTO-1449, including copies of the references contained thereon, for filing in the U.S. Patent and Trademark Office.

You will also find enclosed the associated Transmittals, Electronic Information Disclosure Statements, and United States Patent and Trademark Office Acknowledgment Receipts for the electronically filed Information Disclosure Statement (EFS ID #49914); (EFS ID #49915); (EFS ID#49916); and (EFS ID#49917) filed on October 29, 2003.

The Commissioner is hereby authorized to charge any additional fee or credit overpayment to our Deposit Account No. <u>08-1275</u>. An originally executed duplicate of this transmittal is enclosed for this purpose.

Respectfully submitted,

HAVERSTOCK & OWENS LLP

Dated: 10/29/63

Thomas B. Haverstock

Reg. No.: 32,571

Attorneys for Applicants

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Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313 Group Art Unit: 1763

Examiner: Ram N. Kackar

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

162 N. Wolfe Road Sunnyvale, CA 94086 (408) 530-9700

Sir:

The citations listed below, copies attached, may be material to the examination of the above-identified application, and are therefore submitted in compliance with the duty of disclosure defined in 37 C.F.R. §§ 1.56 and 1.97. The Examiner is requested to make these citations of official record in this application.

United States Patents or Published Patent Applications have been filed electronically (EFS ID #49914); (EFS ID #49915); (EFS ID#49916); and (EFS ID#49917). Applicants have become aware of the following printed publication which may be material to the examination of this application:

- Chinese Publication No. CN 1399790 A;
- German Publication No. DE 36 08 783 A1;
- German Publication No. DE 198 60 084 A1;
- European Publication No. EP 0 244 951 A2;
- European Publication No. EP 0 272 141 A2;
- European Publication No. EP 0 453 867 A1;
- European Publication No. EP 0 572 913 A1;
- European Publication No. EP 0 587 168 A1;
- European Publication No. EP 0 679 753 B1;
 European Publication No. EP 0 903 775 A2;

Attorney Docket No.: <u>SSI-00501</u>

- French Publication No. FR 1 499 491;
- Great Britain Publication No. GB 2 003 975;
- Great Britain Publication No. GB 2 193 482;
- Japanese Patent Abstract JP 2-148841;
- Japanese Patent Abstract JP 2-209729;
- Japanese Patent Abstract JP 11-200035;
- Japanese Patent Abstract JP 56-142629;
- Japanese Patent Abstract JP 60-238479;
- Japanese Patent Abstract JP 60-246635;
- Japanese Patent Abstract JP 61-231166;
- Japanese Patent Abstract JP 62-125619;
- Japanese Patent Abstract JP 63-303059;
- Swiss Publication No. SE 251213;
- PCT Publication No. WO 87/07309;
- PCT Publication No. WO 00/36635;
- PCT Publication No. WO 01/55628 A1;
- PCT Publication No. WO 01/68279 A2;
- PCT Publication No. WO 01/74538 A1;
- PCT Publication No. WO 01/85391 A2;
- PCT Publication No. WO 01/94782 A3;
- PCT Publication No. WO 02/16051 A2;
- PCT Publication No. WO 03/030219 A2;
- Hideaki Itakura et al., "Multi-Chamber Dry Etching System", Solid State Technology, April 1982, pp. 209-214;
- Sun, Y.P. et al., "Preparation of Polymer-Protected Semiconductor Nanoparticles Through the Rapid Expansion of Supercritical Fluid Solution," Chemical Physics Letters, pp. 585-588, May 22, 1998;
- Dahmen, N. et al., "Supercritical Fluid Extraction of Grinding and Metal Cutting Waste Contaminated with Oils," Supercritical Fluids - Extraction and Pollution Prevention, ACS Symposium Series, Vol. 670, pp. 270-279, 21 Oct 1997;
- Xu, C. et al., "Submicron-Sized Spherical Yttrium Oxide Based Phosphors Prepared by Supercritical CO2-Assisted aerosolization and pyrolysis," Appl. Phys. Lett., Vol. 71, No.12, September 22, 1997, pp. 1643-1645;

PATENT Attorney Docket No.: SSI-00501

Courtecuisse, V.G. et al., "Kinetics of the Titanium Isopropoxide Decomposition in Supercritical Isopropyl Alcohol, "Ind. Eng. Chem. Res., Vol. 35, No. 8, pp. 2539-2545, Aug 1996;

- Gallagher-Wetmore, P. et al., "Supercritical Fluid Processing: A New Dry Technique for Photoresist Developing," SPIE Vol. 2438, pp.694-708, Jun. 1995.
- Purtell, R, et al., "Precision Parts Cleaning using Supercritical Fluids," J. Vac, Sci, Technol. A. Vol. 11, No. 4, July 1993, pp. 1696-1701;
- Matson, D.W. et al., "Rapid Expansion of Supercritical Fluid Solutions: Solute Formation of Powders, Thin Films, and Fibers," Ind. Eng. Chem. Res., Vol. 26, No. 11, pp. 2298-2306, 1987;
- Tolley, W.K. et al., "Stripping Organics from Metal and Mineral Surfaces using Supercritical Fluids," Separation Science and Technology, Vol. 22, pp. 1087-1101, 1987;
- Joseph L. Foszcz, "Diaphragm Pumps Eliminate Seal Problems", Plant Engineering, pp. 1-5, February 1, 1996; and
- Bob Agnew, "WILDEN Air-Operated Diaphragm Pumps", Process & Industrial Training Technologies, Inc., 1996.

This Supplemental Information Disclosure Statement under 37 C.F.R. §§ 1.56 and 1.97 is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that anyone or more of these citations constitutes prior art.

> Respectfully submitted, HAVERSTOCK & OWENS LLP

10-24-05

Reg. No.: 32,571

Attorneys for Applicants

CERTIFICATE OF MAILING (27 CFR § 1.8(a))

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FORM PTO-1449 (Modified)

(37 CFR § 1.98(b))

OCT 3 1 2003

U.S. Department of Commerce Patent and Trademark Office

Attorney Docket No.: SSI-00501

Applicants: Maximilian A. Biberger et al.

Serial No.: 09/912,844

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use Several Short of Necessary)

Filing Date: July 24, 2001

Group Art Unit: 1763

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		Dogument					Trans	lation
		Document Number	Publication Date	Country / Patent Office	Class	Subclass	Yes	No
	AA	CN 1399790 A	02/26/03	China	H01L	21/00		x
	AB	DE 36 08 783 A1	09/17/87	Germany	C30B	25/12		x
	AC	DE 198 60 084 A1	07/06/00	Germany	H01L	21/3213		х
	AD	EP 0 244 951 A2	11/11/87	EPO	H01L	21/00		х
	AE	EP 0 272 141 A2	06/22/88	ЕРО	H01L	21/00		х
	AF	EP 0 453 867 A1	10/30/91	EPO	F16K	51/02		Х
	AG	EP 0 572 913 A1	12/08/93	EPO	B01D	11/02		х
-	AH	EP 0 587 168 A1	03/16/94	EPO	B08B	7/00		х
	AI	EP 0 679 753 B1	11/02/95	EPO	D06F	43/00		X
	AJ	EP 0 903 775 A2	03/24/99	EPO	H01L	21/00		Х
	AK	FR 1.499.491	09/18/67	France	F16K			X
•	AL	GB 2 003 975	03/21/79	Great Britain	F04B	43/06		х
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	AN	JP 2-148841	06/07/90	Japan	H01L	21/306		х
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	AW	SE 251213	08/16/48	Swiss	100a			X
	AX	WO 87/07309	12/03/87	PCT	C23C	16/00		х
	AY	WO 00/36635	06/22/00	PCT	H01L	21/00		X
	AZ	WO 01/55628 A1	08/02/01	PCT	F16K	51/02		×
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EXAMINER:

Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (Modified)

U.S. Department of Commerce Patent and Trademark Office

Attorney Docket No.: SSI-00501

Serial No.: 09/912,844

(37 CFR § 1 98(b))	MADEL	ts If Necessary)		· ·				
				Filing Date: July 24, 200	l	Group Art Un	it: 1763	
		FOREIGN PATENTS	OR PUBLISHED FO	REIGN PATENT APPLICA	TIONS			
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	Number	Publication Date	Country	/ Patent Office	Class	Subclass	Yes	No
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BQ	Sun, Y.P. et al., "Pr Chemical Physics I	reparation of Polymer-l Letters, pp. 585-588, M	Protected Semiconduc Iay 22, 1998.	tor Nanoparticles Through t	he Rapid Expan	sion of Supercrit	ical Fluid Sc	olution,"
BR	Dahmen, N. et al., Extraction and Poll	"Supercritical Fluid Ex ution Prevention, ACS	traction of Grinding a Symposium Series, V	nd Metal Cutting Waste Co ol. 670, pp. 270-279, 21 Oc	ntaminated with t 1997.	Oils," Supercriti	cal Fluids -	
BS	Xu, C. et al., "Subr pyrolysis," Appl. P	nicron-Sized Spherical hys. Lett., Vol. 71, No.	Yttrium Oxide Based 12, September 22, 19	Phosphors Prepared by Sup 97, pp. 1643-1645.	ercritical CO2-	Assisted aerosoliz	zation and	
ВТ	Courtecuisse, V.G. Vol. 35, No. 8, pp.	et al., "Kinetics of the 2539-2545, Aug 1996	Titanium Isopropoxid	le Decomposition in Superci	itical Isopropyl	Alcohol, " Ind. E	ng. Chem. R	les.,
BU	Gallagher-Wetmore Jun. 1995.	e, P. et al., "Supercritic	al Fluid Processing: A	New Dry Technique for Ph	otoresist Develo	ping," SPIE Vol	. 2438, pp.6	94-708,
BV	Purtell, R, et al., "P	recision Parts Cleaning	g using Supercritical F	luids, " J. Vac, Sci, Techno	. A. Vol. 11, No	o. 4, July 1993, p	p. 1696-170	1.
BW				olutions: Solute Formation of				
BX	Tolley, W.K. et al., 22, pp. 1087-1101,	"Stripping Organics fr 1987.	om Metal and Minera	l Surfaces using Supercritic	al Fluids," Sepa	ration Science an	d Technolog	gy, Vol.
BY	Joseph L. Foszcz, "	Diaphragm Pumps Elii	minate Seal Problems'	, Plant Engineering, pp. 1-	5, February 1, 19	996.		
BZ	Bob Agnew, "WILI	DEN Air-Operated Dia	phragm Pumps", Proc	ess & Industrial Training Te	chnologies, Inc	, 1996.		
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Page 1 of 2 Fee transmittal

FEE TRANSMITTAL

Electronic Version v08 Stylesheet Version v08.0

Title of Invention

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE

Application Number:

09/912844

09/912844

Date:

2001-07-24

First Named Applicant: Maximilian A. Biberger

Attorney Docket Number:

TOTAL FEE AUTHORIZED \$180

Patent fees are subject to annual revisions on or about October 1st of each year.

BASIC FILING FEE

Fee Description	Fee Code	Amount \$	Fee Paid \$
Submission Of Information Disclosure Stmt Fee	1806	180	180

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Fee transmittal

Page 2 of 2

Access Code

Deposit name:

Haverstock and Owens LLP

Deposit authorized name: Thomas B. Haverstock

Signature:

/tbh/

Date (YYYYMMDD):

2003-10-29

Charge Any Additional Fee Required Under 37 C.F.R. Sections 1.16 and 1.17.

Page 1 of 2 Acknowledgement Receipt

UNITED STATES PATENT AND TRADEMARK OFFICE ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1 Stylesheet Version v1.1.1

Title of Invention	HIGH PRESSURE	PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE
Submission Type:	Information [Disclosure Statement
Application Number:	09/912844	*09/912844*
EFS ID:	49914	
Server Response:	Confirmation Code	Message
	ISVR1	Submission was successfully submitted - Even if Informational or Warning Messages appear below, please do not resubmit this application
	ICON1	5915
	ISYS5	Filename= N/A BusinessRule= Validation System/Function Call Information. #Supporting Msg:Server unable to validate the Confirmaton/Application numbers at this time. They will be checked by PTO personnel later.
First Named Applicant:	Maximilian Bi	berger
Attorney Docket Numbe	r:	
Timestamp:	2003-10-29	12:27:57 EDT
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File Listing:		

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10/29/2003

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Page 2 of 2

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TRANSMITTAL
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Title of Invention HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE

Application Number: 09/912844 *09/912844*

Date: 2001-07-24

First Named Applicant: Maximilian A. Biberger

Confirmation Number: 5915
Attorney Docket Number:

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Submitted by:	Elec. Sign.	Sign. Capacity
Thomas B. Haverstock	/tbh/	
Registered Number: 32571		Attorney

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Files	Documents being submitted

09/912844

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR Title of

SUBSTRATE Invention

09/912844 Application Number: Confirmation Number: 5915

First Named Applicant: Maximilian Biberger

Attorney Docket Number:

Search string: (2617719 or 2625886 or 3744660 or 3968885 or 4029517 or

4091643 or 4245154 or 4341592 or 4355937 or 4367140 or 4406596 or 4422651 or 4474199 or 4522788 or 4549467 or 4592306 or 4601181 or 4626509 or 4670126 or 4682937 or 4693777 or 4749440 or 4778356 or 4789077 or 4823976 or 4825808 or 4827867 or 4838476 or 4865061 or 4879431 or 4917556 or 4924892 or 4951601 or 4960140 or 4983223 or 5011542 or 5044871 or 5062770 or 5071485 or 5105556 or 5167716 or 5169296 or 5169408 or 5186718 or 5188515 or

5190373 or 5191993).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	2617719	1952-11-11	C. R. Stewart	7		
	2	2625886	1953-01-20	Browne	٦		
	3	3744660	1973-07-10	Gaines et al.	_		
	4	3968885	1976-07-13	Hassan et al.	7		
	5	4029517	1977-06 14	Rand	7		
	6	4091643	1978-05-30	Zucchini			
	7	4245154	1981-01-13	Uehara et al.			
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4474199 1984-10-02 Blaudszun 13 14 4522788 1995-06-11 Sitek et al. Wilden et al. 4549467 1985-10-29 15 Gallego 16 4592306 1986-06-03 17 4601181 1986-07-22 Privat 18 4626509 1986-12-02 Lyman 4670126 1987-06-02 Messer et al. 19 20 4682937 1987-07-28 Credle, Ir. 4693777 1987-09-15 Hazano et al. 21 22 4749440 1988-06-07 Blackwood et al. 4778356 1988-10-18 23 24 4789077 1988-12-06 Noe 25 4823976 1989-04-25 White, III et al. 26 4825808 1989-05-02 Takahashi et al. Takei et al. 4827867 1989-05-09 27 28 4838476 1989-06-13 Rahn 1989-09-12 29 4865061 Fowler et al. 30 4879431 1989-11-07 Bertoncini 4917556 1990-04-17 Stark et al 31 32 4924892 1990-05-15 Kiba et al. 33 4951601 1990-08-28 Maydan et al. 34 4960140 1990-10-02 ishijima et al. 35 4983223 1991-01-08 Gessner 36 5011542 1991-04-30 Weil 37 5044871 1991-09-03 Davis et al. 38 5062770 1991-11-05 Story et al.

1991-12-10

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Shortes et al.

Mack et al.

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Information Disclosure Statement

Page 3 of 3

40	5105556	1992-04-21	Kurokawa et al.
41	5167716	1992-12 01	Boitnott et al.
42	5169296	1992-12 08	Wilden
43	5169408	1992-12-08	Biggerstaff et al.
44	5186718	1993-02-16	Tepman et al.
45	5188515	1993- 02-23	Horn
46	5190373	1993-03-02	Dickson et al.
47	5191993	1993 -03-09	Wanger et al.

Remarks

Note: Remarks are not for responding to an office action.

Non US Patent and Publication references shall be filed under a separate paper transmittal. The current electronic filing contains part 1 out of a total of 4 electronic filings.

Signature

	Examiner Name	 Date
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UNITED STATES PATENT AND TRADEMARK OFFICE ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1 Stylesheet Version v1.1.1

Title of Invention	HIGH PRESSURE	PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE
Submission Type:	Information (Disclosure Statement
Application Number:	09/912844	*09/912844*
EFS ID:	49915	
Server Response:	Confirmation Code	Message
	ISVR1	Submission was successfully submitted – Even if Informational or Warning Messages appear below, please do not resubmit this application
	ICON1	5915
	ISYS5	Filename = N/A BusinessRule = Validation System/Function Call Information. #Supporting Msg:Server unable to validate the Confirmation/Application numbers at this time. They will be checked by PTO personnel later.
First Named Applicant:	Maximilian B	iberger
Attorney Docket Number	:	
Timestamp:	2003-10-29	12:37:0 7 EDT
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Page 2 of 2

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Page 2 of 2

Transmittal

Electronic Version v1.1

TRANSMITTAL

Stylesheet Version v1.1.0

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE Invention Title of

09/912844 09/912844 Application Number:

Maximilian A. Biberger 2001-07-24 First Named Applicant:

Confirmation Number: 5915

Attorney Docket Number:

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Submitted by:	Elec. Sign.	Sign. Capacity
Thomas B. Haverstock	/tbh/	
Registered Number: 32571		Attorney

Documents being submitted	Files
us-ids	SSI00501B-usidst.xml
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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

> HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR Title of SUBSTRATE Invention

09/912844 Application Number: Confirmation Number:

09/912844

First Named Applicant: Maximilian Biberger

Attorney Docket Number:

Search string:

(\$193560 or \$195878 or \$213485 or \$221019 or \$222876 or 5224504 or 5236669 or 5240390 or 5243821 or 5246500 or 5251776 or 5280693 or 5285352 or 5288333 or 5339844 or 5370741 or 5412958 or 5433334 or 5447294 or 5503176 or 5505219 or 5509431 or 5571330 or 5589224 or 5621982 or 5629918 or 5644855 or 5649809 or 5656097 or 5669251 or \$702228 or \$706319 or \$746008).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

	init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
۱	-	1	5193560	1993-03-16	Tanaka et al.]		
H		2	5195878	1993-03-23	Sahiavo et al.]		
H		3	5213485	1993-05 -25	Wilden]		
		4	5221019	1993-06-22	Pechacek]		
		5	5222876	1993-06-29	Budde			
		6	5224504	1993-07-06	Thompson et al.]		
П		7	5236669	1993-08-17	Simmons et al.]		
Ш		8	5240390	1993-08-31	Kvinge et al.]		
		9	5243821	1993-09-14	Schuck et al.]		
		10	5246500	1993-09-21	Samata et al.]		

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	Examiner Name	Date	
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	11	5251776	1993-10-12	Morgan Jr. et al.
	12	5280693	1994-01-25	Heudecker
	13	5285352	1994-02-08	Pastore et al.
	14	5288333	1994-02-22	Tanaka et al.
	15	5339844	1994-08-23	Stanford Jr. et al.
\Box	16	5370741	1994-12-06	Bergman
M	17	5412958	1995-05-09	iliff et al.
	18	5433334	1995-07-18	Reneau
	19	5447294	1995-09-05	Sakata et al.
	20	5503176	1996-04-02	Dunmire et al.
	21	5505219	1996-04-09	Lansberry et al.
T	22	5509431	1996-04-23	Smith, Jr. et al.
	23	5571330	1996-11-05	Kyogoku
	24	5589224	1996-12-31	Tepman et al.
	25	5621982	1997-04-22	Yamashita et al.
	26	5629918	1997-05-13	Ho et al.
	27	5644855	1997-07-08	McDermott et al.
	28	5649809	1997-07-22	Stapelfeldt
	29	5656097	1997-08-12	Olesen et al.
	30	5669251	1997-09-23	Townsend et al.
	31	5702228	1997-12-30	Tamai et al.
	32	5706319	1998-01-06	Holtz
	33	5746008	1998-05-05	Yamashita et al.

Remarks

Note: Remarks are not for responding to an office action.

Non US Patent and Publication references shall be filed under a separate paper transmittal. The current electronic filing contains part 2 out of a total of 4 electronic filings. Fee has been paid in previous electronic filing.

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UNITED STATES PATENT AND TRADEMARK OFFICE ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1 Stylesheet Version v1.1.1

Title of Invention	HIGH PRESSURE	PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE
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Application Number:	09/912844	*09/912844*
EFS ID:	49916	
Server Response:	Confirmation Code	Message
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First Named Applicant:	Maximilian Bi	berger
Attorney Docket Numbe	r:	
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10/29/2003

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Page 2 of 2

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Page 2 of 2

Transmittal

TRANSMITTAL

Electronic Version v1.1

Stylesheet Version v1.1.0

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE Invention Title of

09/912844 09/912844 Application Number:

2001-07-24

Maximilian A. Biberger First Named Applicant:

Confirmation Number: 5915

Attorney Docket Number:

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Submitted by:	Elec. Sign.	Sign. Capacity
Thomas B. Haverstock	/tbh/	
Registered Number: 32571		Attorney

Documents being submitted	Files
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	us-ids.xsl
Comments	

09/912844

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

> HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR Title of SUBSTRATE Invention

Application Number: 09/912844

Confirmation Number: 5915

First Named Applicant: Maximilian Biberger Attorney Docket Number:

(5900107 or 5904737 or 5932100 or 5934991 or 5981399 or Search string: 5989342 or 6005226 or 6017820 or 6029371 or 6037277 or 6053348 or 6056008 or 6077053 or 6082150 or 6085935 or 6097015 or 6128830 or 6145519 or 6159295 or 6164297 or 6203582 or 6216364 or 6239038 or 6241825 or 6251250 or 6277753 or 6286231 or 6305677 or 6334266 or 6344174 or 6388317 or 6389677 or 6418956 or 6436824 or 6454945 or

6464790).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

1	5900107	1999-05-04	Murphy et al.	7		_
2	5904737	1999-05-18	Preston et al.	j		
3	5932100	1999-08-03	Yager et al.]		
4	5934991	1999-08- 10	Rush	7		
5	5981399	1999-11 -09	Kawamura et al.	7		
6	5989342	1999-11-23	Ikeda et al.	7		
7	6005226	1999-12-21	Aschner et al.]		
8	6017820	2000-01-25	Ting et al.]		
9	6029371	2000-02-29	Kamikawa et al.	٦		
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Information Disclosure Statement

Page 3 of 3

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Signature

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1 11	10 [6037277	2000-03-14	Masakara et al.	ı	
┝	11	6037277	2000-03-14	Masakara et al.		
<u> </u> _					{	
	12	6056008	2000-05-02	Adams et al.]	
	13	6077053	2000-06-20	Fujikawa et al.]	
	14	6082150	2000-07-04	Stucker]	
	15	6085935	2000-07-11	Malchow et al.]	
	16	6097015	2000-08-01	McCullough et al.		
Ĭ	17	6128830	2000-10-10	Bettcher et al.)	
	18	6145519	2000-11-14	Konishi et al.)	
	19	6159295	2000-12-12	Maskara et al.]	
T	20	6164297	2000-12-26	Kamikawa]	
	21	6203582	2001-03-20	Berner et al.	B1	
	22	6216364	2001-04-17	Tanaka et al.	B1	
	23	6239038	2001-05-29	Wen	81	
Ti	24	6241825	2001-06-05	Wytman	В1]
	25	6251250	2001-06-26	Keigler	Bl]
	26	6277753	2001-08-21	Mullee et al.	BI	
	27	6286231	2001-09-11	Bergman et al.	В1	
	28	6305677	2001-10-23	Lenz	B1	
	29	6334266	2002-01-01	Moritz et al.	BI	
	30	6344174	2002-02-05	Miller et al.	BI]
	31	6388317	2002-05-14	Reese	BI)
	32	6389677	2002-05-21	Lenz	Bì)
	33	6418956	2002-07-16	Bloom	B1]
	34	6436824	2002-08-20	Chool et al.	В١]
	35	6454945	2002-09-24	Weig! et al.	Bì]
	36	6464790	2002-10-15	Shertinsky et al.	В١	Ì

Remarks

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UNITED STATES PATENT AND TRADEMARK OFFICE ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1 Stylesheet Version v1.1.1

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Submission Type: Application Number: EFS ID:	Information E 09/912844 49917	oisclosure Statement *09/912844*			
Server Response:	Confirmation Code	Message			
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First Named Applicant:					

Attorney Docket Number:

Timestamp:

2003-10-29 12:43:21 EDT

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Page 2 of 2

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Electronic Version v1.1

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HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE Invention Title of

09/912844 09/912844 Application Number:

2001-07-24

Thomas 8. Haverstock First Named Applicant:

Confirmation Number: 5915

Attorney Docket Number:

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Submitted by:	Elec. Sign.	Sign. Capacity
Maximilian A. Biberger	/tbh/	
Registered Number: 32571		Attorney

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Comments		us-ids.xsl
	Comments	

09/912844

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v1 8 Stylesheet Version v18.0

Title of

Invention

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR

SUBSTRATE

Application Number: 09/912844

Confirmation Number: 5915

First Named Applicant: Thomas Haverstock

Attorney Docket Number:

Search string:

(6521466 or 6541278 or 6546946 or 6550484 or 6558475 or 6561213 or 6561220 or 6561481 or 6561767 or 6564826 or

5217043 or 20020001929).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

1	init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
		1	6521466	2002-02-18	Castrucci	BI		
		2	6541278	2003-04-01	Morita et al.	BI		
		3	6546946	2003-04-15	Dunmire	Bl		
	Ī.	4	6550484	2003-04-22	Gopinath et al.	ВІ		
		5	6558475	2003-05-06	Jur et al.	В1		
		6	6561213	2003-05-13	Wang et al.	BI		
١.		7	6561220	2003-05-13	McCullough et al.	BI		
ľ		8	6561481	2003-05-13	Filonczuk	ВІ		
		9	6561767	2003-05-13	Biberger et al.	В1		
		10	6564826	2003-05-20	Shen	ВІ		
	—	11	5217043	1993-06-08	Novakovi			
1								

US Published Applications

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init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
		20020001929	2002-01-03	Biberger et al.	Al		``

Remarks

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